

<u>26a</u>	<u>27b</u>	<u>27b</u>	<u>27b</u>	<u>26c</u>
<u>27a</u>	<u>28</u>	<u>28</u>	<u>28</u>	<u>27c</u>
<u>27a</u>	<u>28</u>	<u>28</u>	<u>28</u>	<u>27c</u>
<u>26b</u>	<u>27d</u>	<u>27d</u>	<u>27d</u>	<u>26d</u>

FIG. 4

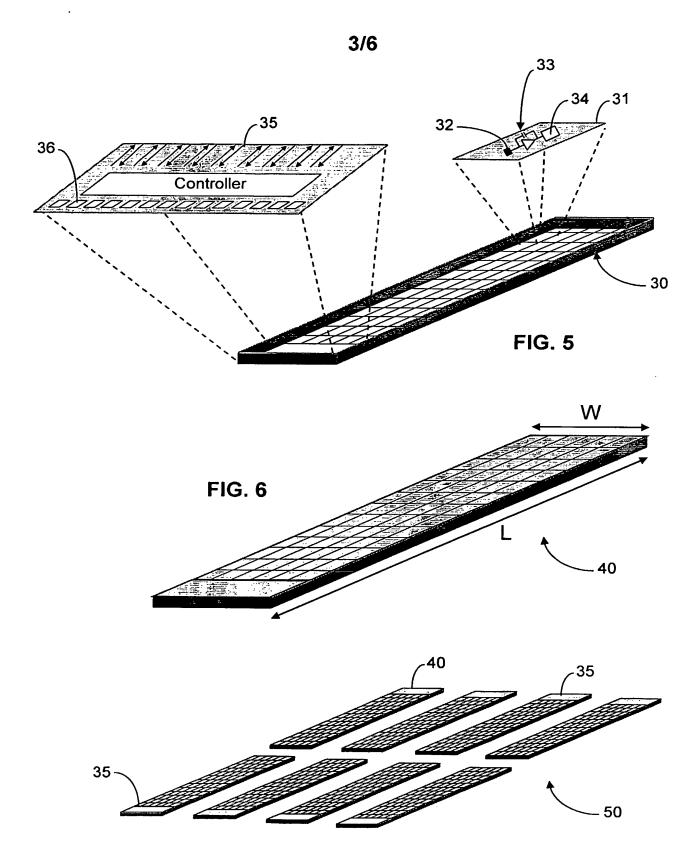


FIG. 7

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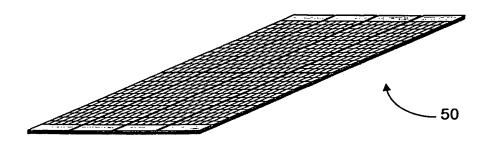
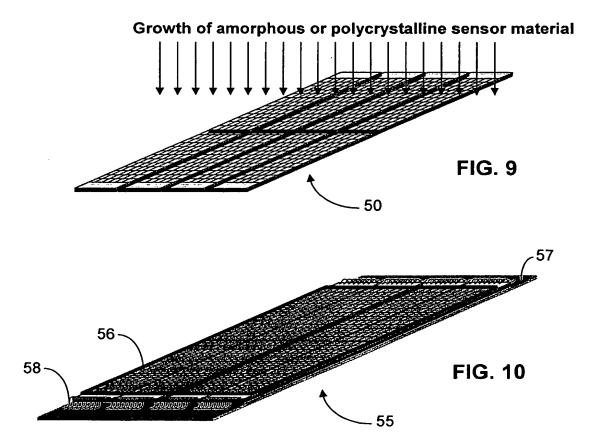
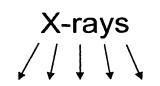
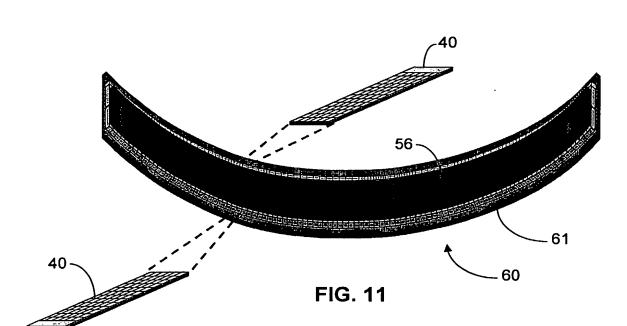


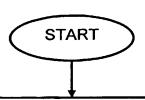
FIG. 8







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FORM A VERY LARGE AREA INTEGRATED CIRCUIT HAVING AT LEAST ONE ARRAY OF ELECTRONIC PROCESSING CIRCUITS EACH HAVING A RESPECTIVE SENSOR INPUT THAT IS ACCESSIBLE FROM A FIRST SURFACE OF THE INTEGRATED CIRCUIT

DEPOSIT AMORPHOUS OR POLYCRYSTALLINE SENSOR MATERIAL ON THE FIRST SURFACE OF THE WAFER SO AS TO FORM AN ARRAY OF DIODES, EACH HAVING A FIRST ELECTRODE WHICH IS IN OHMIC CONTACT WITH A RESPECTIVE ONE OF THE SENSOR INPUTS AND SUCH THAT THE EXPOSED SURFACE OF THE SENSOR MATERIAL FORMS A COMMON SECOND ELECTRODE OF OPPOSITE POLARITY TO THE FIRST ELECTRODE TOWARDS WHICH INCIDENT PHOTONS ARE DIRECTED

END

FIG. 12